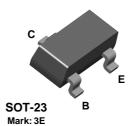


MPSH10

MMBTH10





NPN RF Transistor

This device is designed for use in low noise UHF/VHF amplifiers, with collector currents in the 100 μA to 20 mA range in common emitter or common base mode of operations, and in low frequency drift, high output UHF oscillators. Sourced from Process 42.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	М	Units	
		MPSH10	*MMBTH10	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/∘C
R _{eJC}	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter Test Conditions		Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	25		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	30		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	3.0		V
I _{СВО}	Collector Cutoff Current	$V_{CB} = 25 \text{ V}, I_{E} = 0$		100	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_{C} = 0$		100	nA

ON CHARACTERISTICS

h _{FE}	DC Current Gain	$I_C = 4.0 \text{ mA}, V_{CE} = 10 \text{ V}$	60		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 4.0 \text{ mA}, I_B = 0.4 \text{ mA}$		0.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 4.0 \text{ mA}, V_{CE} = 10 \text{ V}$		0.95	V

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_C = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$	650		MHz
		f = 100 MHz			
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		0.7	pF
C _{rb}	Common-Base Feedback Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$	0.35	0.65	pF
rb'C _c	Collector Base Time Constant	$I_C = 4.0 \text{ mA}, V_{CB} = 10 \text{ V},$		9.0	pS
	N.	f = 31.8 MHz			

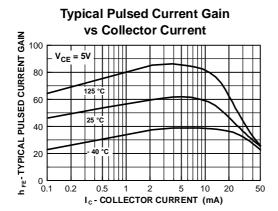
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

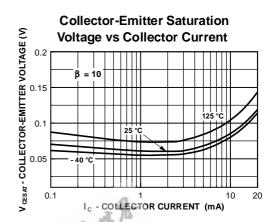
Spice Model

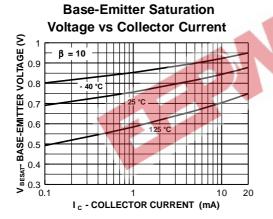
 $NPN \ (Is=69.28E-18 \ Xti=3 \ Eg=1.11 \ Vaf=100 \ Bf=308.6 \ Ne=1.197 \ Ise=69.28E-18 \ Ikf=22.83m \ Xtb=1.5 \ Br=1.11 \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=4 \ Cjc=1.042p \ Mjc=.2468 \ Vjc=.75 \ Fc=.5 \ Cje=1.52p \ Mje=.3223 \ Vje=.75 \ Tr=1.558n \ Tf=135.8p \ Itf=.27 \ Vtf=10 \ Xtf=30 \ Rb=10)$

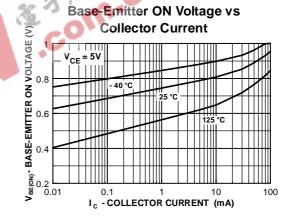
(continued)

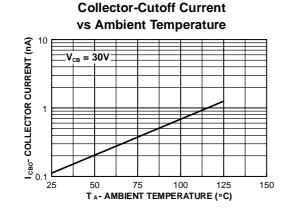
Typical Characteristics

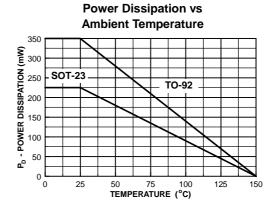






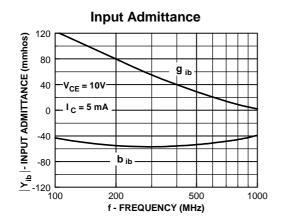


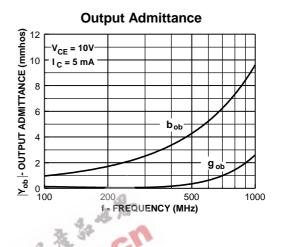


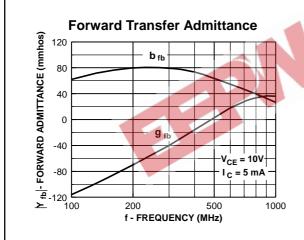


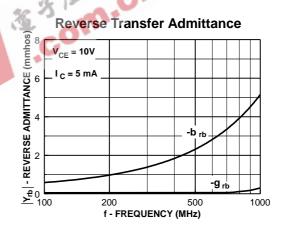
(continued)

Common Base Y Parameters vs. Frequency







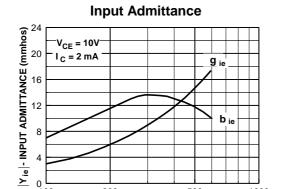


(continued)

Common Emitter Y Parameters vs. Frequency

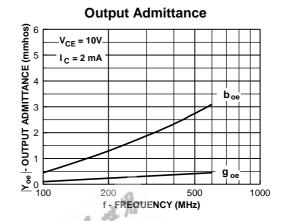
500

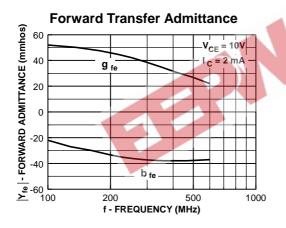
1000

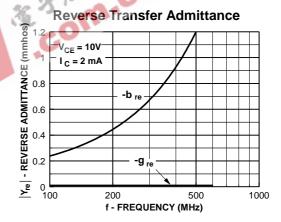


f - FREQUENCY (MHz)

100







(continued)

Test Circuits

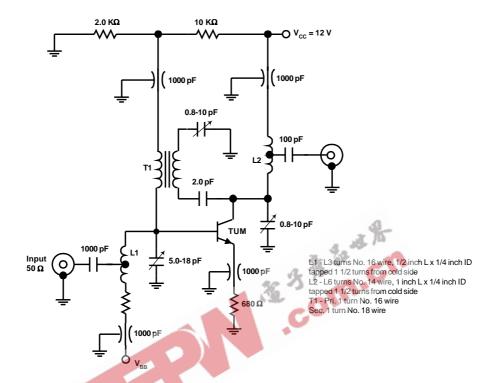


FIGURE 1: Neutralized 200 MHz PG and NF Circuit

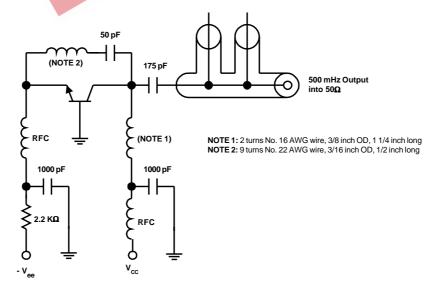
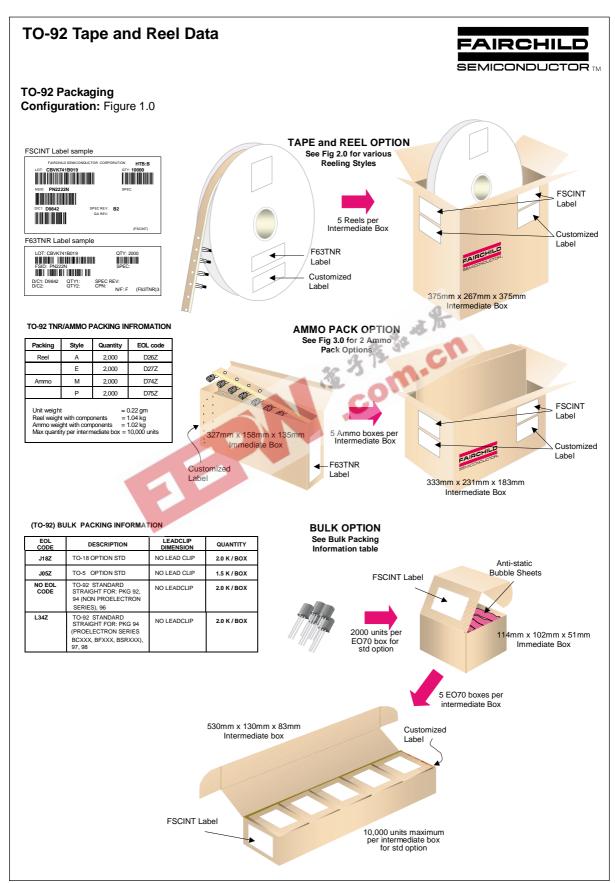


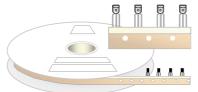
FIGURE 2: 500 MHz Oscillator Circuit



TO-92 Tape and Reel Data, continued

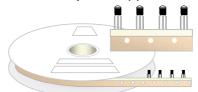
TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)



Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging

Configuration: Figure 3.0

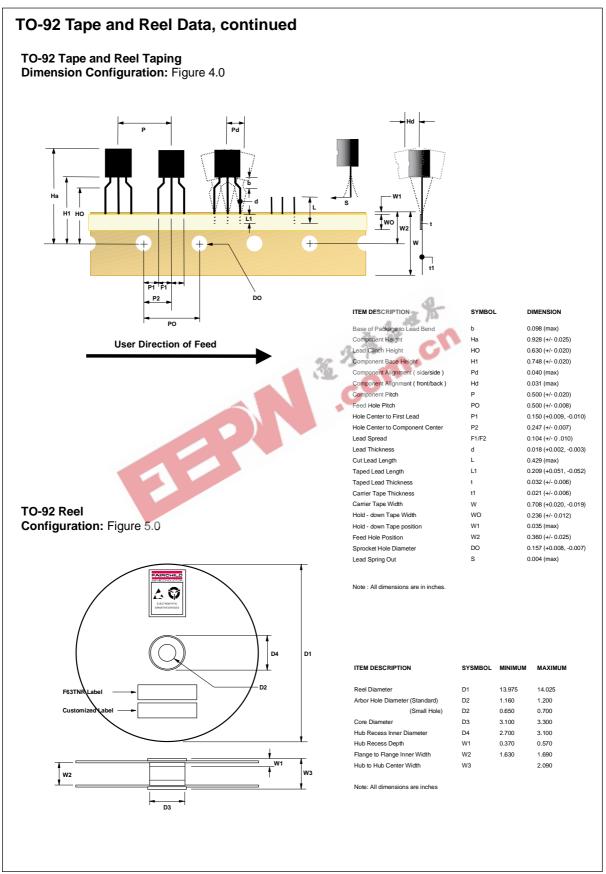
FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON TOP ORDER STYLE D74Z (M)

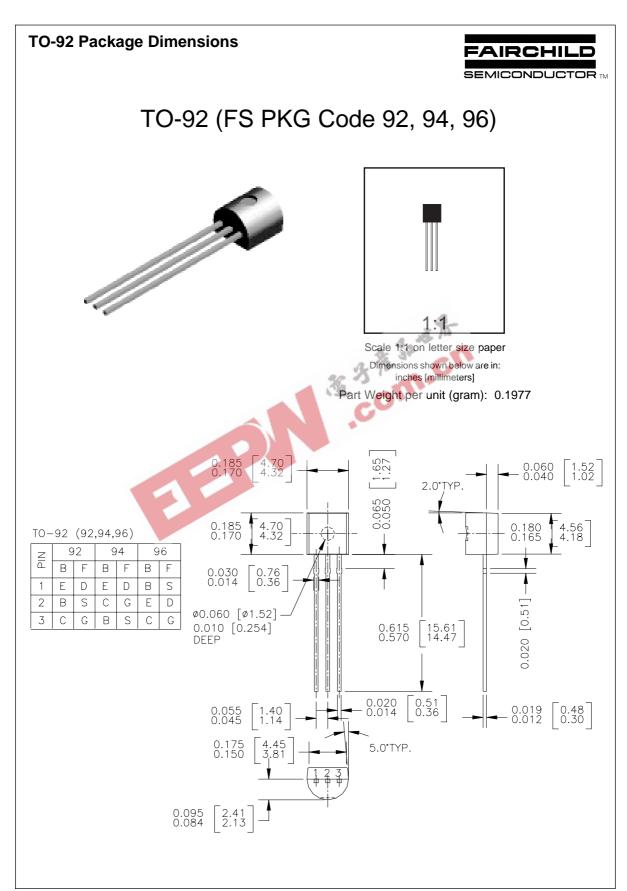
FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM

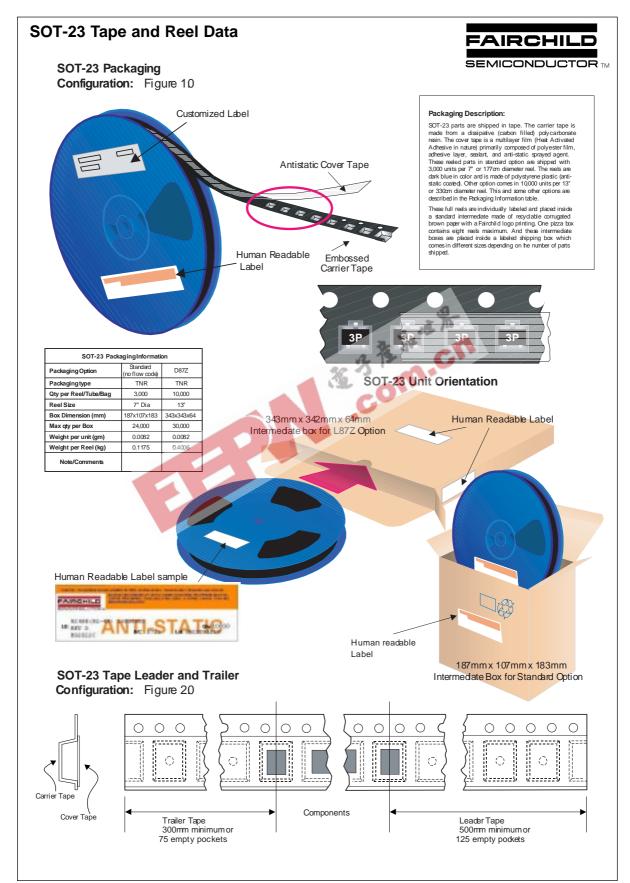
FIRST WIRE OFF IS EMITTER ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM

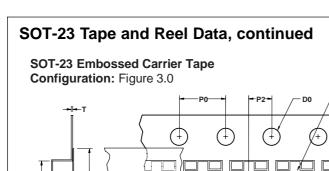


FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP









User Direction of Feed

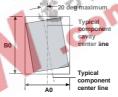
	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	КО	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



SOT-23 Reel Configuration: Figure 4.0

Sketch A (Side or Front Sectional View)
Component Rotation



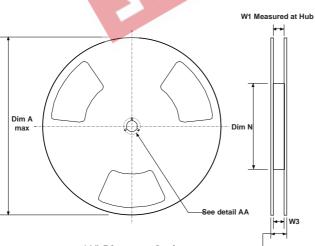
(+)

Sketch B (Top View)
Component Rotation

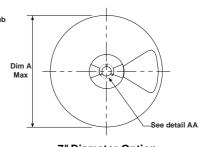


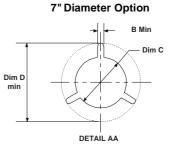
Sketch C (Top View)

Component lateral movement



13" Diameter Option W2 max Measured at Hub



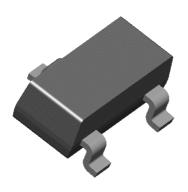


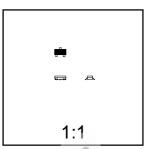
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SOT-23 Package Dimensions



SOT-23 (FS PKG Code 49)

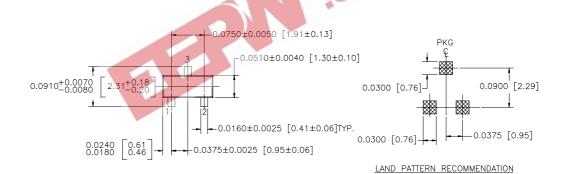


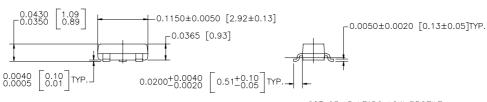


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS SOT 23, 3 LEADS LOW PROFILE

NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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CROSSVOLT™	HiSeC™	QT Optoelectronics™	VCX^{TM}
DOME™	ISOPLANAR™	Quiet Series™	
E ² CMOS™	MICROWIRE™	SILENT SWITCHER ®	
EnSigna™	OPTOLOGIC™	SMART START™	
FACT™	OPTOPLANAR™	SuperSOT™-3	
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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